

## N Channel MOSFET



Lead Free Package and Finish

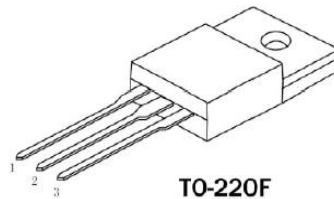
### Applications:

- Adapter & Charger
- SMPS Standby Power
- AC-DC Switching Power Supply
- LED driving power

$I_D$	$R_{DS(ON)}(Typ.)$	$V_{DSS}$
10A	0.92Ω	800V

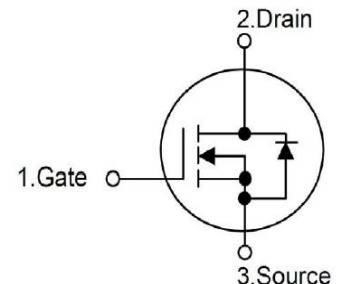
### Features:

- Low On Resistance
- Low Gate Charge
- Peak Current vs Pulse Width Curve
- RoHS Compliant



TO-220F

Not to Scale



### Ordering Information

Part Number	Package	Marking
RS10N80F	TO-220F	RS10N80F

### Absolute Maximum Ratings $T_c=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	RS10N80F	Units
$V_{DSS}$	Drain-to-Source Voltage (Note*1)	800	V
$I_D$	Continuous Drain Current	10	A
$I_{D@ 100^{\circ}\text{C}}$	Continuous Drain Current	6.3	
$I_{DM}$	Pulsed Drain Current (Note*2)	40	
$P_D$	Power Dissipation	62	W
	Derating Factor above $25^{\circ}\text{C}$	0.5	W/ $^{\circ}\text{C}$
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulse Avalanche Energy $L=30\text{mH}$ $I_{AS}=7.5\text{A}$ $V_{DD}=100\text{V}$ $R_G=25\Omega$ $T_J=25^{\circ}\text{C}$	938	mJ
$T_L$ TPKG	Maximum Temperature for Soldering	300 260	$^{\circ}\text{C}$
	Leads at 0.063in(1.6mm)from Case for 10 seconds		
	Package Body for 10 seconds		
$T_J$ and $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to 150	

\*Drain Current Limited by Maximum Junction Temperature

Caution:Stresses greater than those listed in the“Absolute Maximum Ratings”Table may cause permanent damage to the device.

### Thermal Resistance

Symbol	Parameter	RS10N80F	Units	Test Conditions
$R_{\theta JC}$	Junction-to-Case	2.02	$^{\circ}\text{C}/\text{W}$	Drain lead soldered to water cooled heatsink, $P_D$ adjusted for a peak junction temperature of $+150^{\circ}\text{C}$ .
$R_{\theta JA}$	Junction-to-Ambient	62.5		1 cubic foot chamber,free air.

### OFF Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$BV_{DSS}$	Drain-to-source Breakdown Voltage	800	--	--	v	$V_{GS}=0V, I_D=250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	1.0	$\mu A$	$V_{DS}=800V, V_{GS}=0V$
$I_{GSS}$	Gate-to-Source Forward Leakage	--	--	100	nA	$V_{GS}=+30V, V_{DS}=0V$
	Gate-to-Source Reverse Leakage	--	--	-100		$V_{GS}=-30V, V_{DS}=0V$

### ON Characteristics $T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	--	0.92	1.15	$\Omega$	$V_{GS}=10V, I_D=5.0A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{GS}=V_{DS}, I_D=250\mu A$

### Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	23	--	nS	$V_{DS}=400V$ $I_D=10A$ $R_G=25\Omega$ (Note:3,4)
$t_{rise}$	Rise Time	--	15	--		
$t_{d(OFF)}$	Turn-OFF Delay Time	--	90	--		
$t_{fall}$	Fall Time	--	30	--		

### Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$C_{iss}$	Input Capacitance	--	1979	--	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0MHz$
$C_{oss}$	Output Capacitance	--	133	--		
$C_{rss}$	Reverse Transfer Capacitance	--	53	--		
$Q_g$	Total Gate Charge	--	83	--	nC	$V_{DS}=640V$ $I_D=10A$ $V_{GS}=10V$ (Note:3,4)
$Q_{gs}$	Gate-to-Source Charge	--	9	--		
$Q_{gd}$	Gate-to-Drain("Miller") Charge	--	49	--		

## Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current	--	--	10	A	Integral pn-diode in MOSFET
$I_{SM}$	Maximum Pulsed Current	--	--	40	A	
$V_{SD}$	Diode Forward Voltage	--	--	1.4	V	$I_S=10A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	320	--	nS	$V_{GS}=0V$
$Q_{rr}$	Reverse Recovery Charge	--	4.2	--	$\mu C$	$I_S=10A, di/dt=100A/\mu s$

### Notes:

- \*1.  $T_J = \pm 25^\circ C$  to  $+150^\circ C$ .
- \*2. Repetitive rating; pulse width limited by maximum junction temperature.
- \*3. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 1\%$ .
- \*4. Basically not affected by temperature.

## Typical Feature curve

Figure1. Typical Output Characteristics

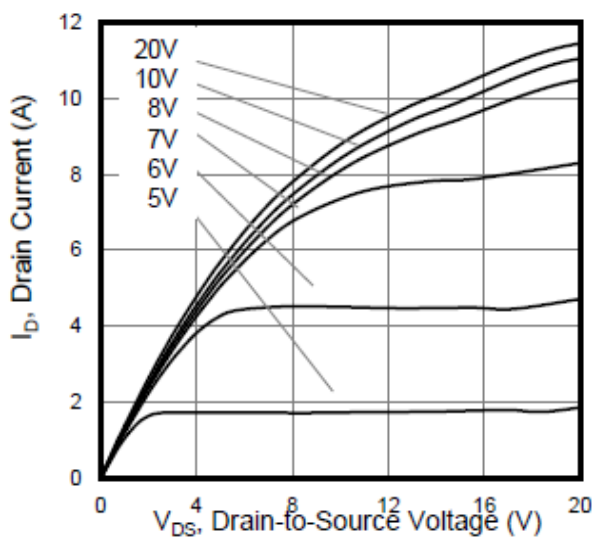
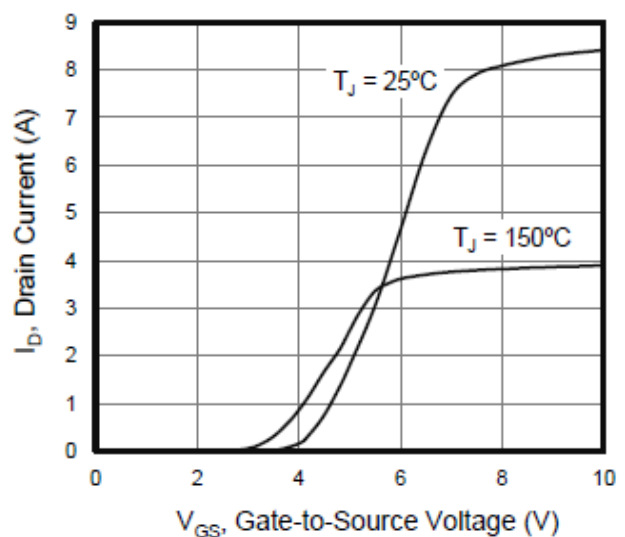
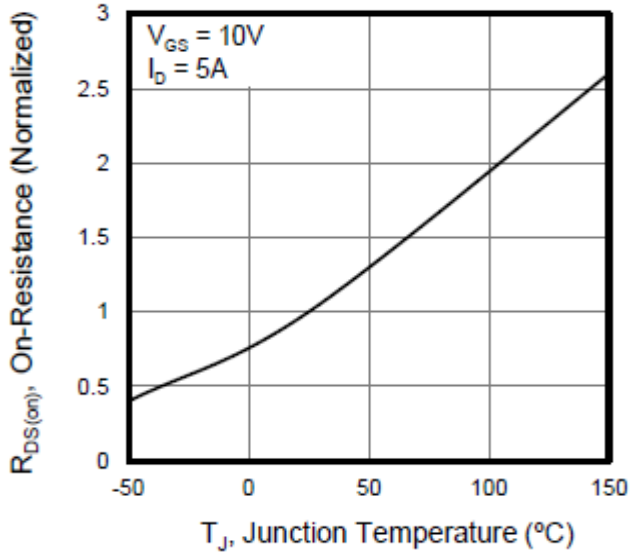


Figure2. Typical Transfer Characteristics



Figuer3. Typical ON Resistance vs Temperature



Figuer4. Typical Body Diode Transfer Characteristics

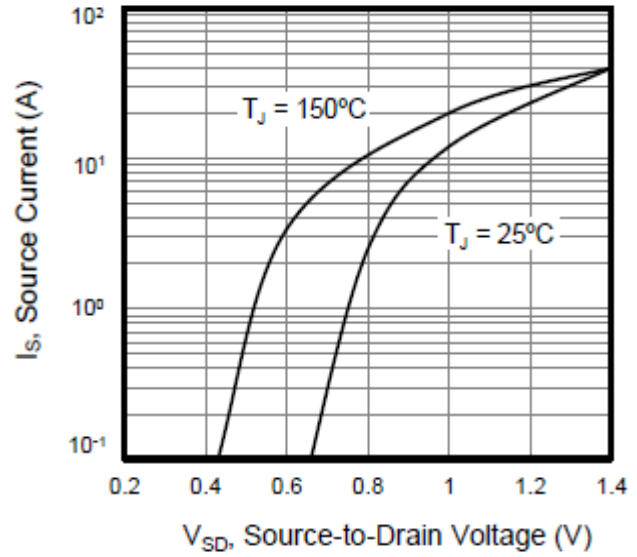


Figure5. Typical Drain Current vs. Temperature

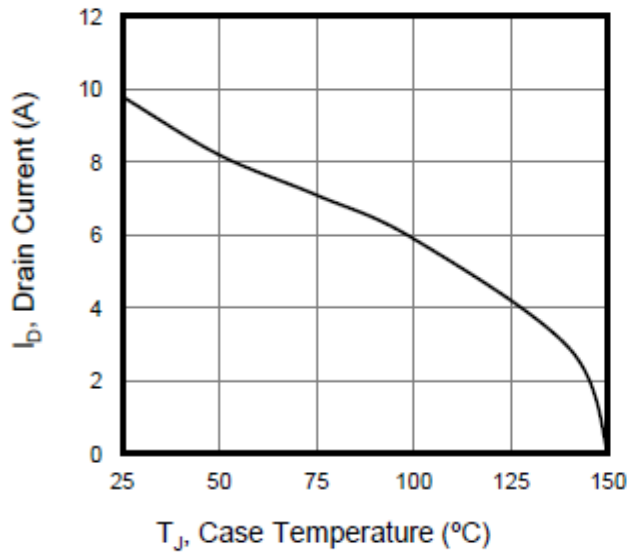


Figure6. BVDSS Variation vs. Temperature

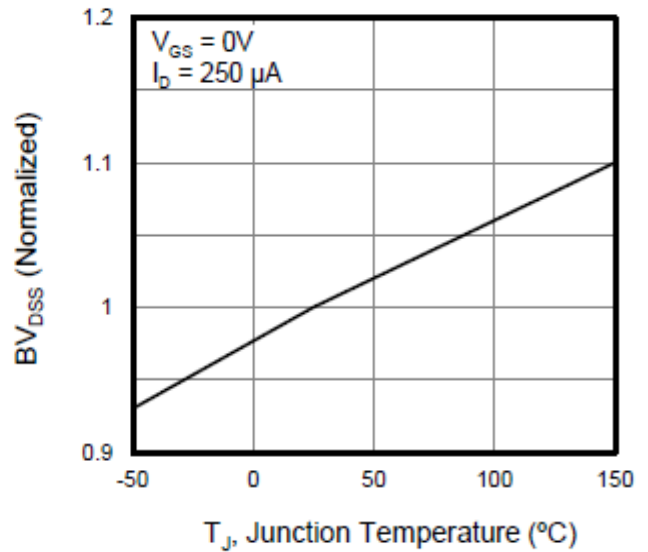


Figure7. Capacitance

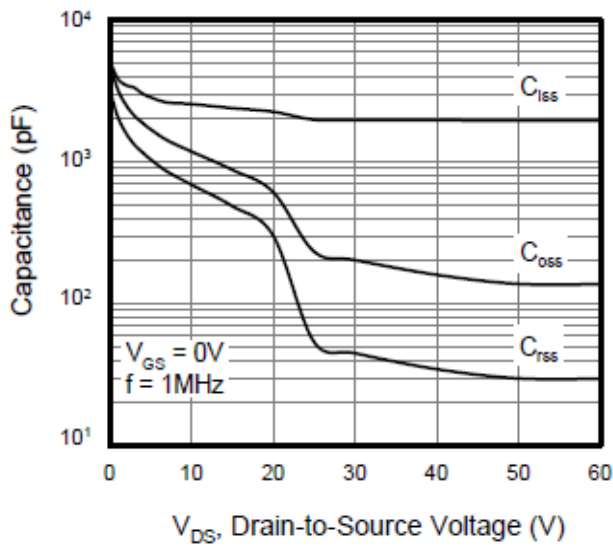


Figure8. Gate Charge

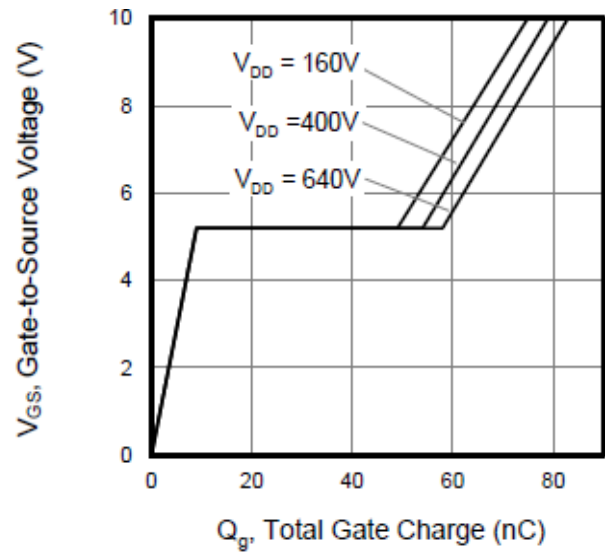
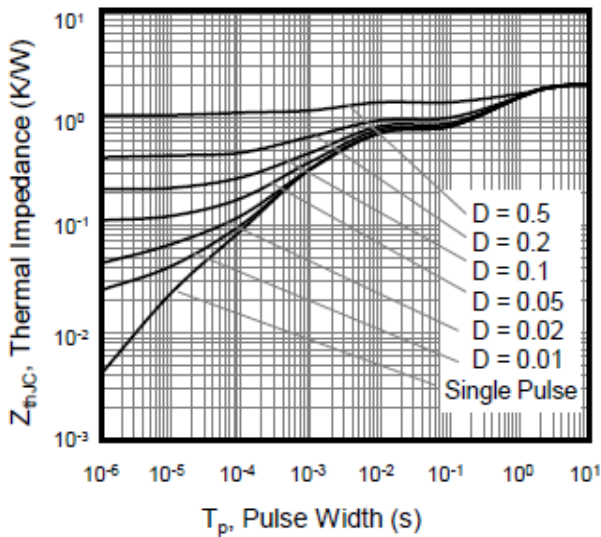


Figure9. Transient Thermal Impedance



**Test Circuits and Waveforms**

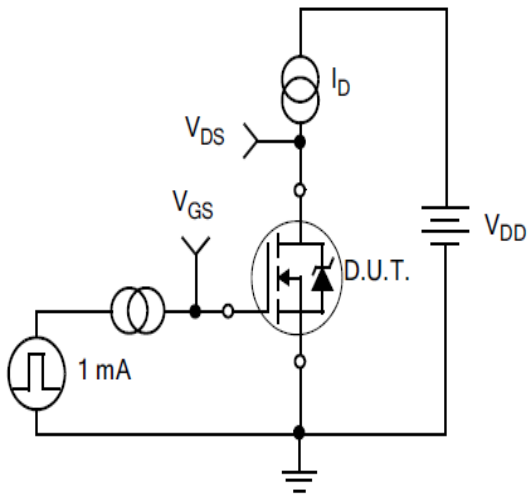


Figure11.  
Gate Charge Test Circuit

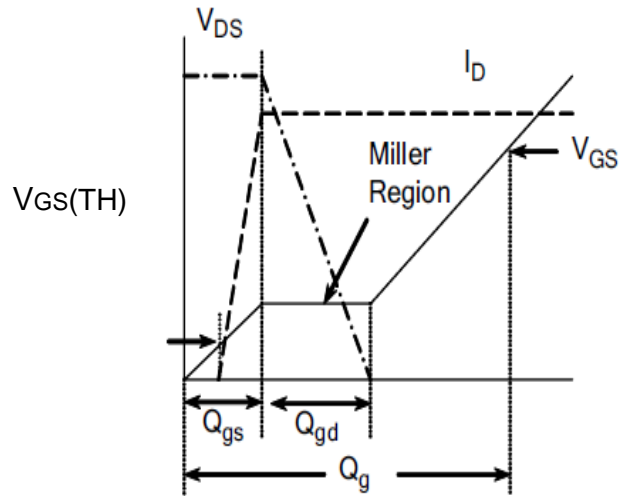


Figure12.  
Gate Charge Waveform

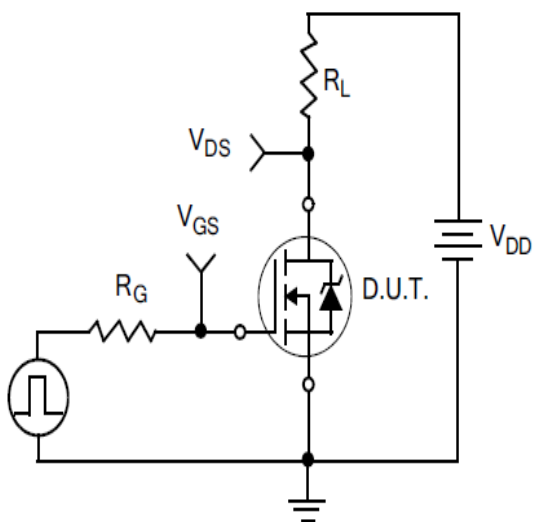


Figure13.  
Resistive Switching Test Circuit

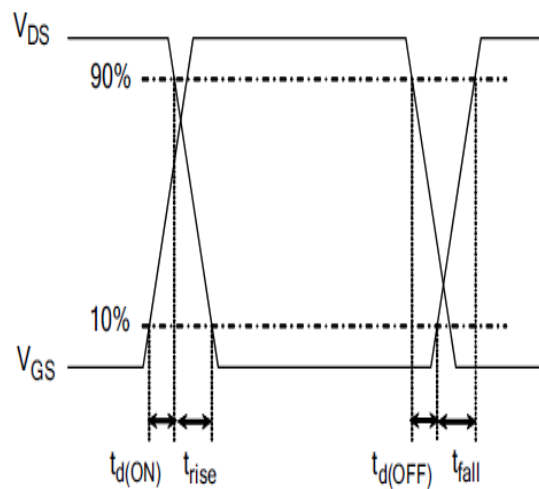


Figure14.  
Resistive Switching Waveforms

Test Circuits and Waveforms

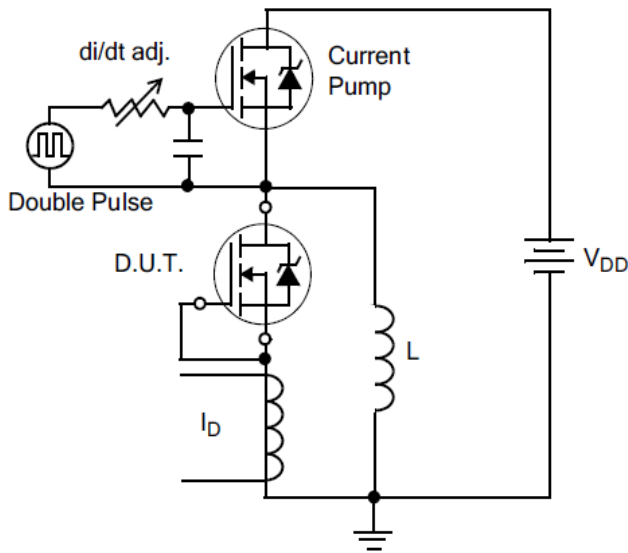


Figure15.Diode Reverse Recovery Test Circuit

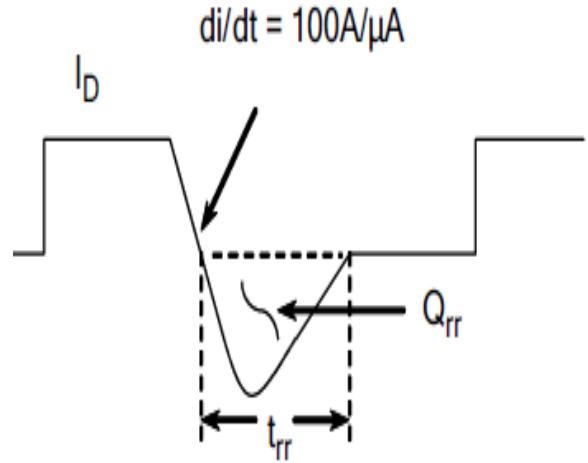


Figure16.Diode Reverse Recovery Waveform

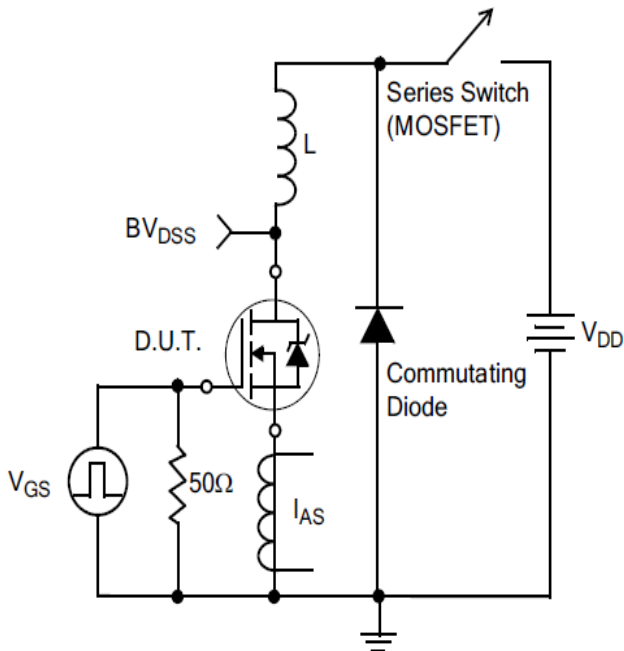
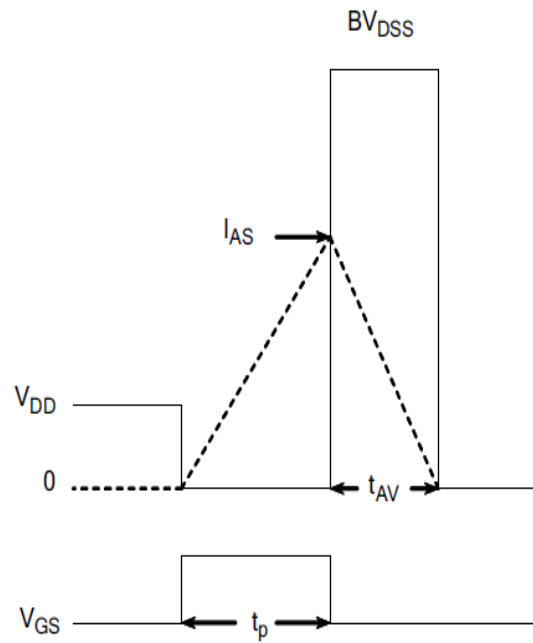


Figure17.Unclamped Inductive Switching Test Circuit

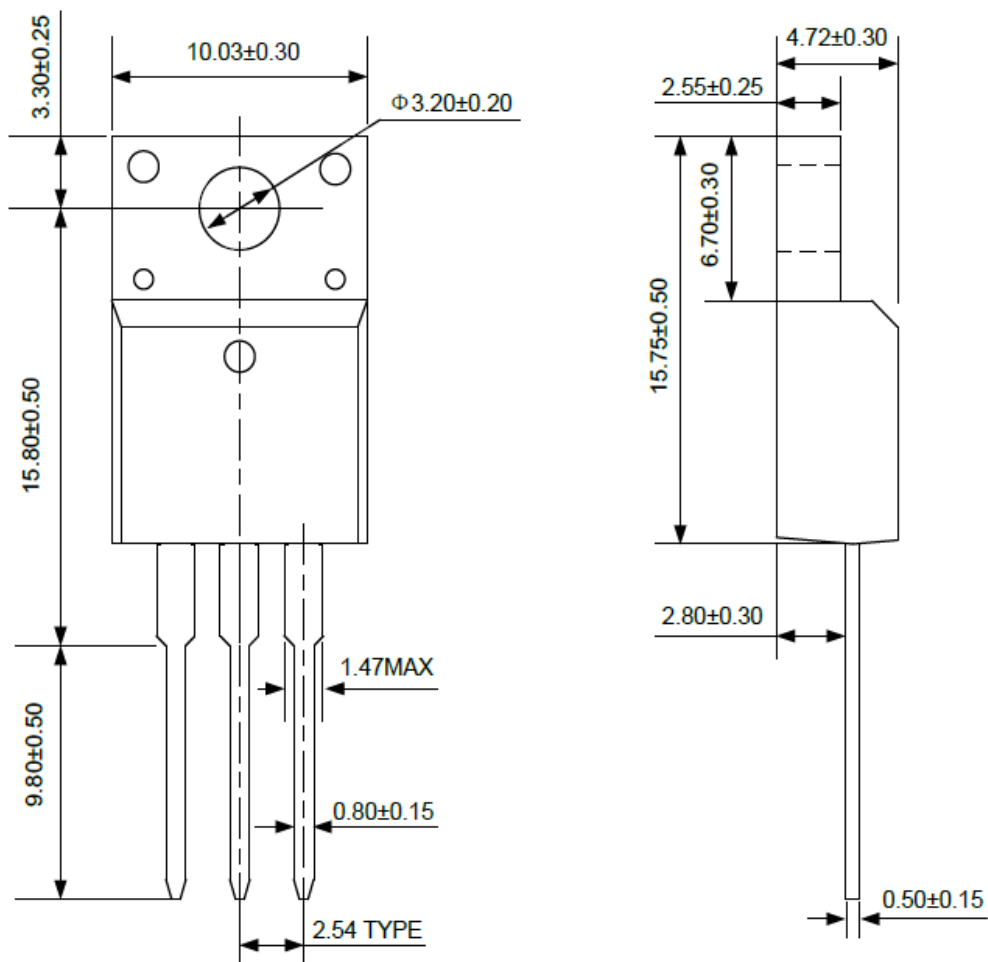


$$EAS = \frac{IAS^2 L}{2}$$

Figure18.Unclamped Inductive Switching Waveforms

Package outline drawing

Unit: mm



TO-220F



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